

P-Channel Power MOSFET

● General Description

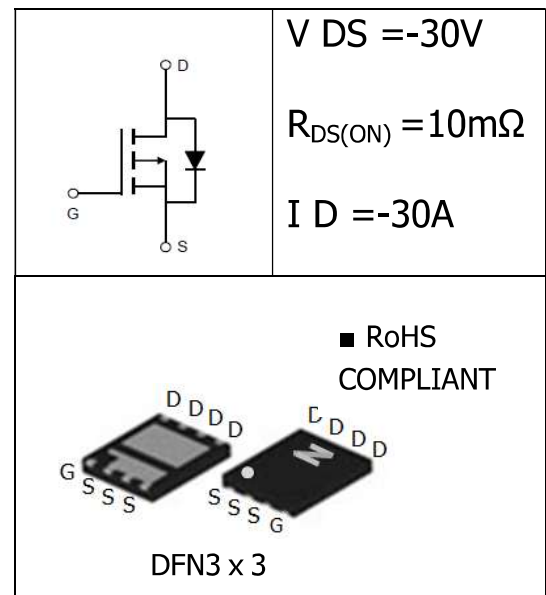
The AP30P30Q combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. This device is ideal for load switch and battery protection applications.

● Features

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance

● Application

- MB/VGA Vcore
- SMPS 2nd Synchronous Rectifier
- POL application
- BLDC Motor driver



● Ordering Information:

Marking	30P30
Packing	REEL TAPE
Basic ordering unit (pcs)	5000
Normal Package Material Ordering Code	AP30P30Q-TAP
Halogen Free Ordering Code	AP30P30Q-TAP-HF

● Absolute Maximum Ratings ($T_c = 25^\circ C$)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ($T_C = 25^\circ C$)	I_D	-30	A
Pulsed Drain Current ^①	I_{DM}	-90	A
Total Power Dissipation ^②	$P_D @ T_C = 25^\circ C$	40	W
Total Power Dissipation	$P_D @ T_A = 25^\circ C$	1.5	W
Operating Junction Temperature	T_J	-55 to 150	$^\circ C$
Storage Temperature	T_{STG}	-55 to 150	$^\circ C$

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●Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case ^②	R_{thJC}	-	-	34	° C/W
Thermal resistance, junction - ambient	R_{thJA}	-	-	180	° C/W
Soldering temperature, wavesoldering for 10s	T_{sold}	-	-	265	° C

●Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-30			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS}=V_{DS}, I_D=-250\mu A$	-0.8		-2.0	V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=-30V, V_{GS}=0V$			-1.0	μA
Gate- Source Leakage Current	I_{GSS}	$V_{GS}=\pm 12V, V_{DS}=0V$			± 100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	$V_{GS}=-10V, I_D=-15A$		7	10	m Ω
		$V_{GS}=-4.5V, I_D=-8A$		10	13	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=-10V, I_D=-5A$		9		s

●Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C_{iss}	$f = 1MHz$	-	2150	-	pF
Output capacitance	C_{oss}		-	430	-	
Reverse transfer capacitance	C_{rss}		-	320	-	

●Gate Charge characteristics($T_a = 25^\circ C$)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Total gate charge	Q_g	$V_{DD} = 15V$	-	35	-	nC
Gate - Source charge	Q_{gs}	$I_D = 15A$	-	5	-	
Gate - Drain charge	Q_{gd}	$V_{GS} = 10V$	-	10	-	

Note: ① Pulse Test : Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$;

② Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate;

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Typical Electrical and Thermal Characteristics

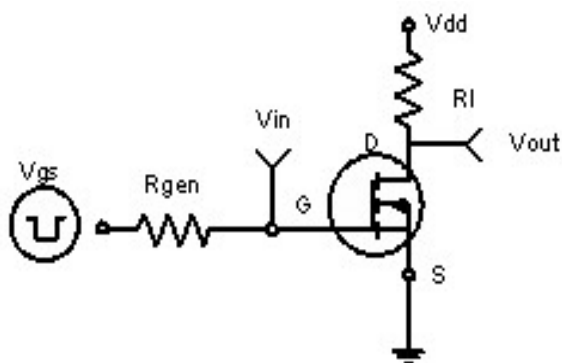


Figure 1 Switching Test Circuit

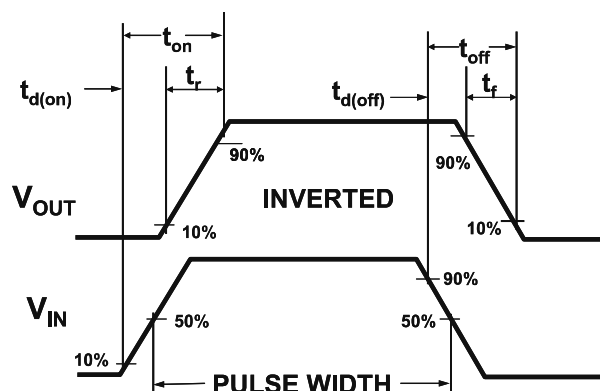


Figure 2 Switching Waveforms



Figure 3 Power Dissipation

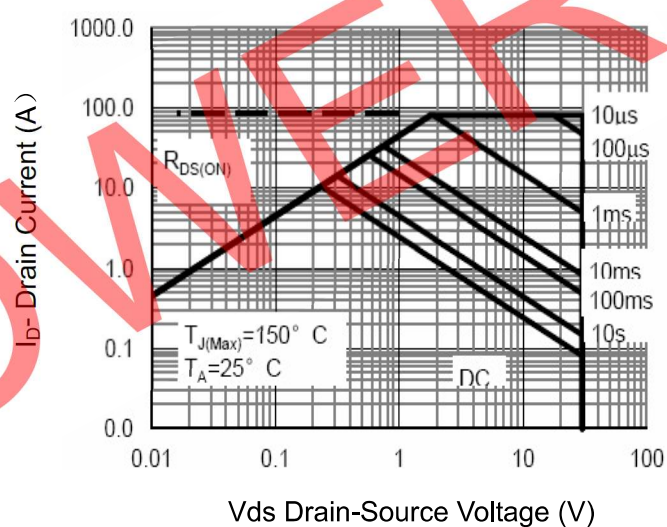


Figure 4 Safe Operation Area

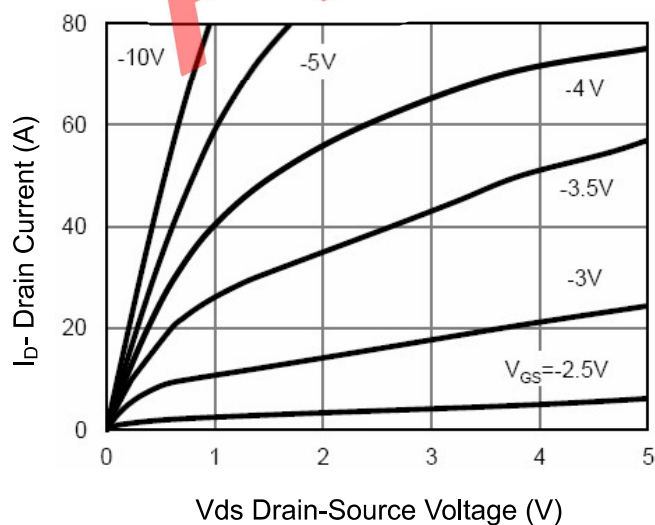


Figure 5 Output Characteristics

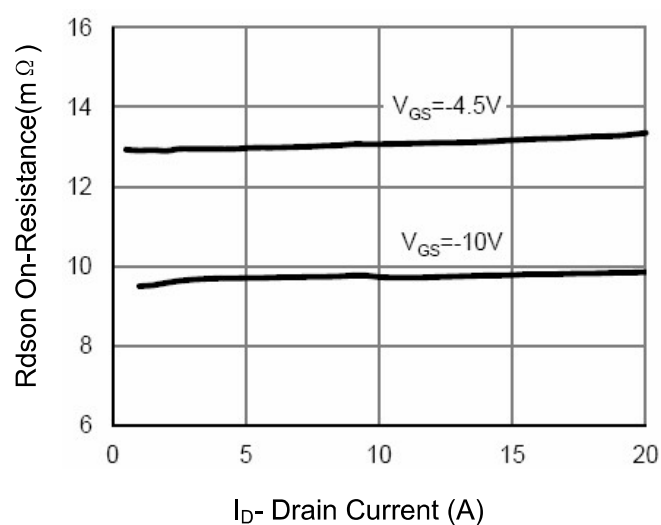


Figure 6 Drain-Source On-Resistance

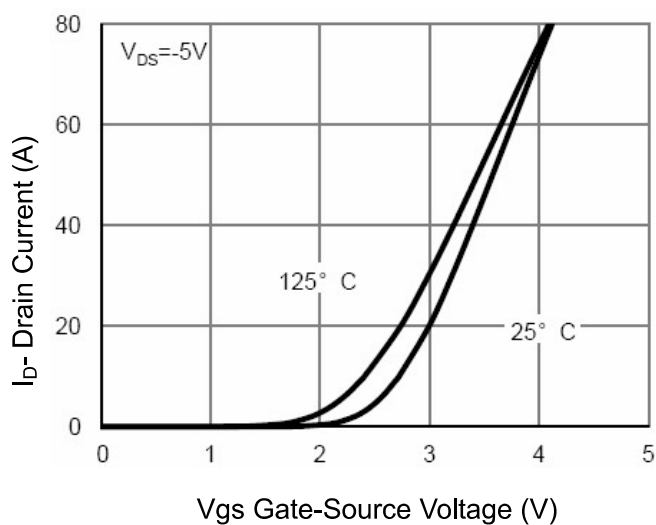


Figure 7 Transfer Characteristics

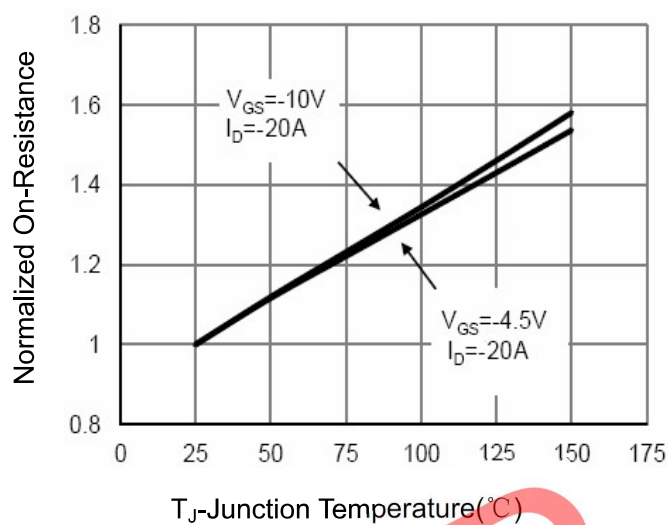


Figure 8 Drain-Source On-Resistance

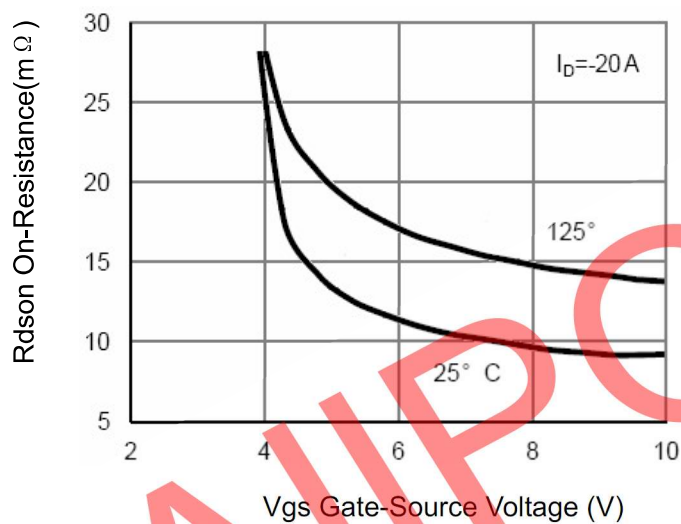


Figure 9 $R_{DS(on)}$ vs V_{GS}

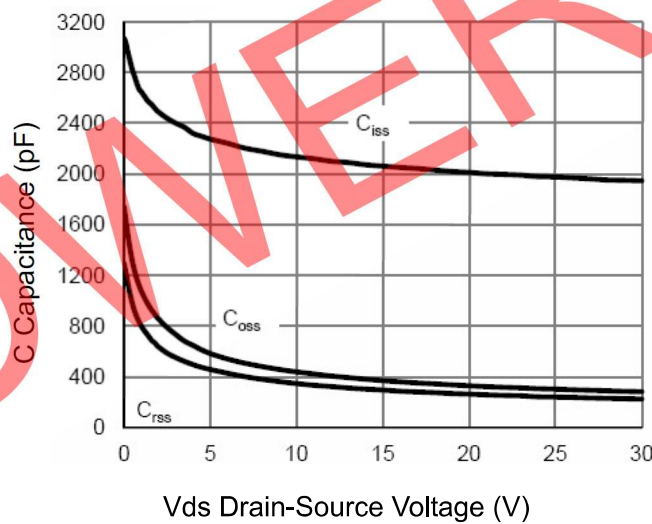


Figure 10 Capacitance vs V_{DS}

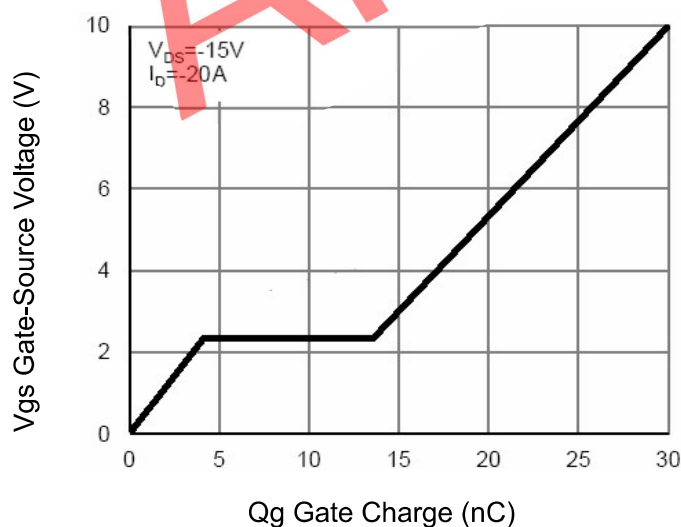


Figure 11 Gate Charge

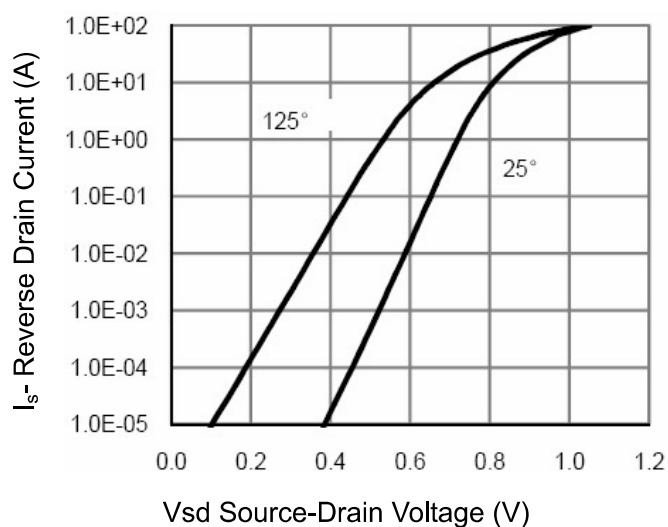
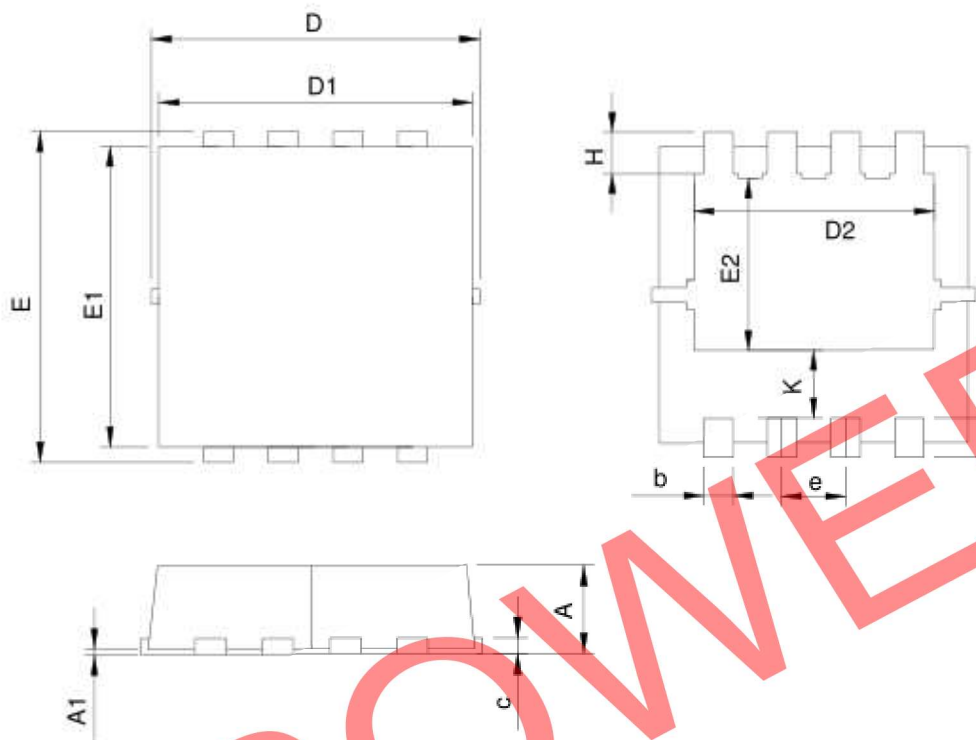


Figure 12 Source- Drain Diode Forward

AP30P30Q

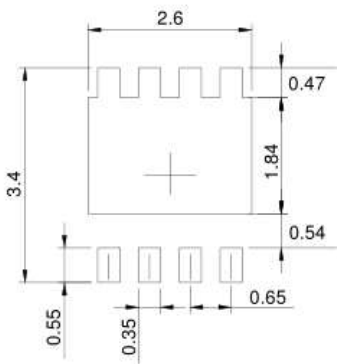
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•Dimensions(DFN3×3)



Symbol	DFN3.3x3.3-8			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	0.70	1.00	0.028	0.039
A1	0.00	0.05	0.000	0.002
b	0.25	0.35	0.010	0.014
c	0.14	0.20	0.006	0.008
D	3.10	3.50	0.122	0.138
D1	3.05	3.25	0.120	0.128
D2	2.35	2.55	0.093	0.100
E	3.10	3.50	0.122	0.138
E1	2.90	3.10	0.114	0.122
E2	1.64	1.84	0.065	0.072
e	0.65 BSC		0.026 BSC	
H	0.32	0.52	0.013	0.020
K	0.59	0.79	0.023	0.031
L	0.25	0.55	0.010	0.022

RECOMMENDED LAND PATTERN



UNIT: mm